N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	340A
$R_{DS(ON)}$(at V_{GS}=10V)	1.3m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D	40	-	-	V
		V_{GS}= 0V, I_D=1mA	40	-		

Typical Electrical and Thermal Characteristics Diagrams

Figure 1. Output Characteristics

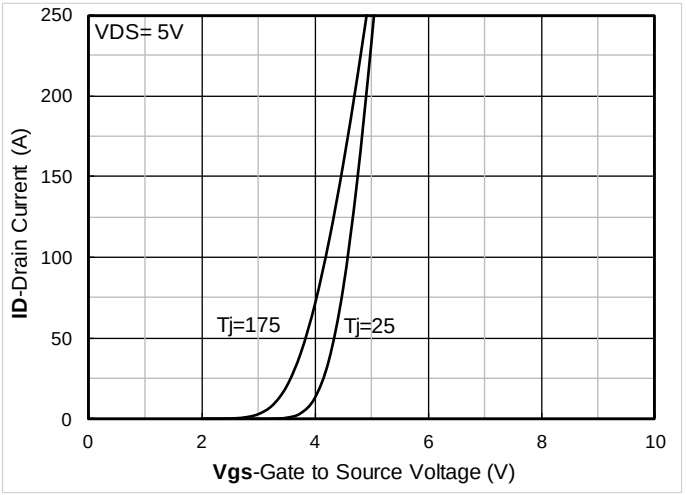


Figure 2. Transfer Characteristics

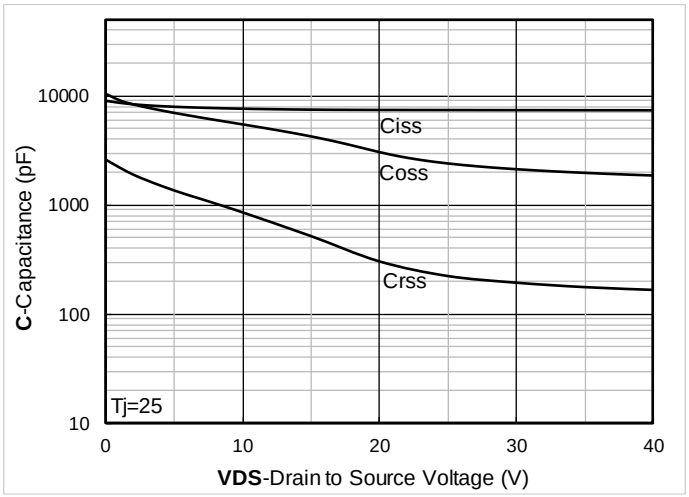


Figure 3. Capacitance Characteristics

Figure 4. Gate Charge

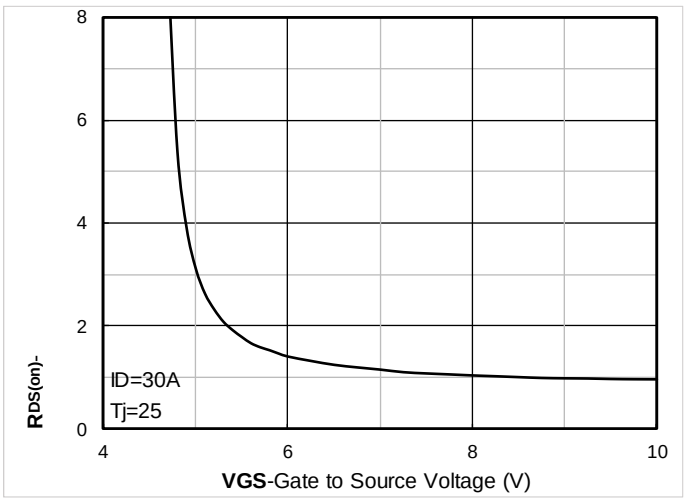


Figure 5. On-Resistance vs Gate to Source Voltage

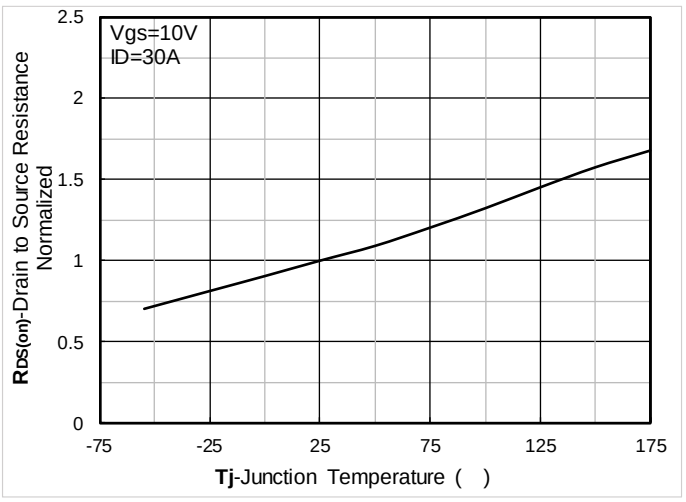
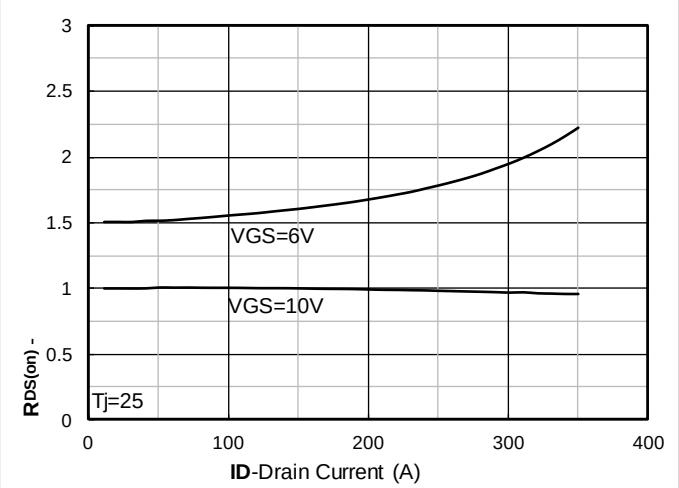


Figure 6. Normalized On-Resistance



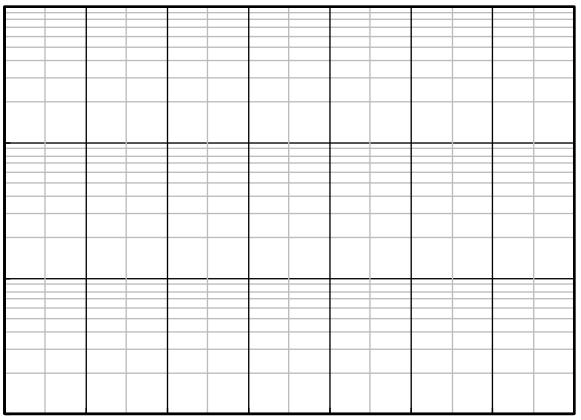


Figure 7. $R_{DS(on)}$

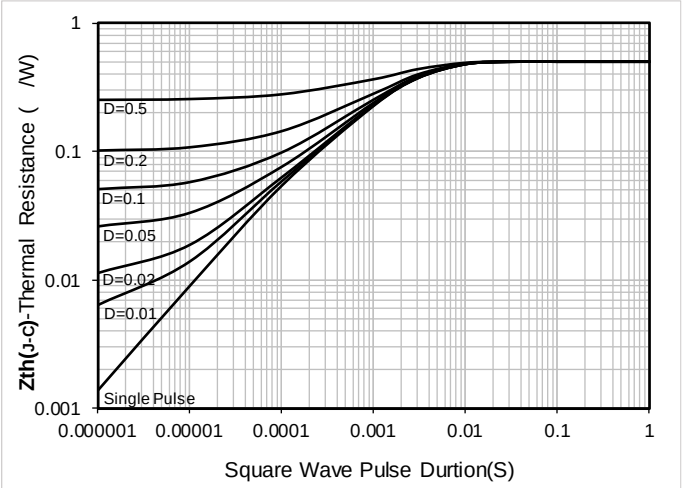


Figure 13. Maximum Transient Thermal Impedance

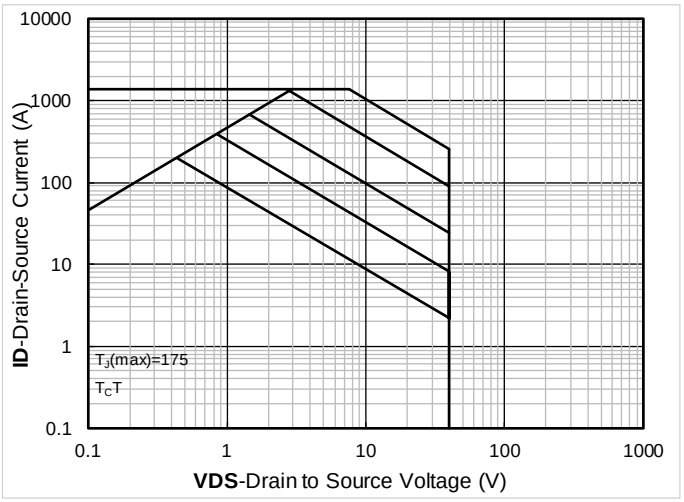


Figure 14. Safe Operation Area

Test Circuits & Waveforms

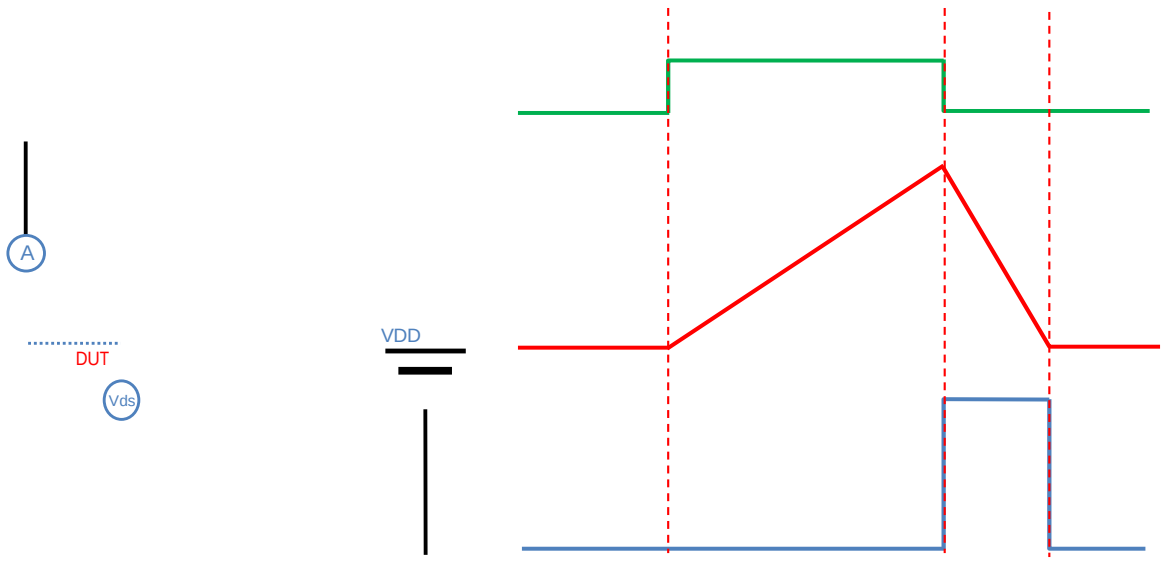


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

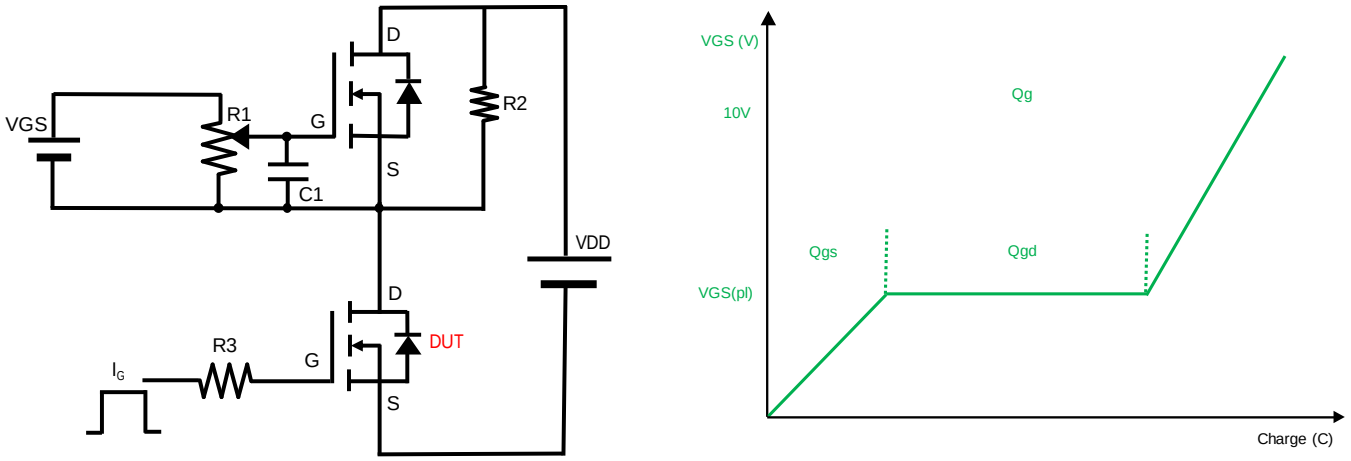


Figure B. Gate Charge Test Circuit & Waveform

TOLL Package information

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4		

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.03mm.
3.The pad layout is for reference purposes only.

SUGGESTED SOLDER PAD LAYOUT
TOP VIEW

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics,are not designed for use in medical, life-saving, lifesustaining,or